

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 7,683,454 B2
APPLICATION NO. : 10/762592
DATED : March 23, 2010
INVENTOR(S) : Jean-Baptiste Quoirin et al.

Page 1 of 1

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Col. 1, line 41 should read:

--direction of arrows I illustrated in Figs. 1A and 1B in a--.

Col. 4, line 14 should read:

--indicated by arrows I is likely to flow horizontally from the--.

Col. 8, claim 22, line 42 should read:

--extending through the substrate being contacted by at--.

claim 26, line 59 should read:

--The IGBT transistor of claim 21, wherein each of the--.

Col. 9, claim 31, line 13, should read:

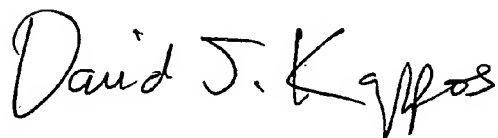
--through an entire thickness of the semiconductor chip.--.

Col. 10, claim 44, line 25, should read:

--contacts extending through the substrate, wherein the first--.

Signed and Sealed this

Eleventh Day of May, 2010

A handwritten signature in black ink, reading "David J. Kappos". The signature is written in a cursive, flowing style with a large initial 'D' and 'K'.

David J. Kappos
Director of the United States Patent and Trademark Office